## 1. General description

NPN high-voltage low  $V_{CEsat}$  transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package. PNP complement: PBHV9115T-Q.

### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_{\text{C}}$  and  $I_{\text{CM}}$
- High collector current gain (hFE) at high IC
- Small SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	150	V
I <sub>C</sub>	collector current		-	-	1	Α
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	250	-	



150 V, 1 A NPN high-voltage low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		j
3	С	collector		В —
				 E
			1	sym021

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PBHV8115T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBHV8115T-Q	W6%

[1] % = placeholder for manufacturing site code

150 V, 1 A NPN high-voltage low VCEsat transistor

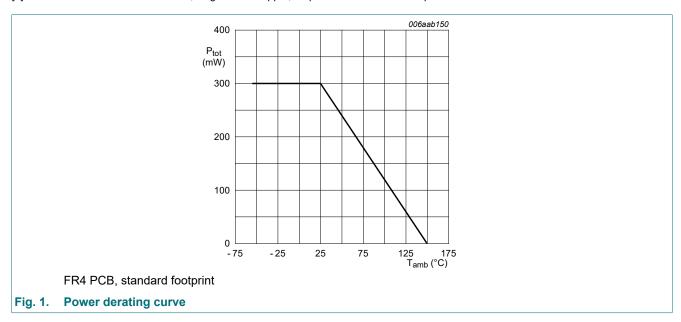
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	400	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	150	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>BM</sub>	peak base current			-	400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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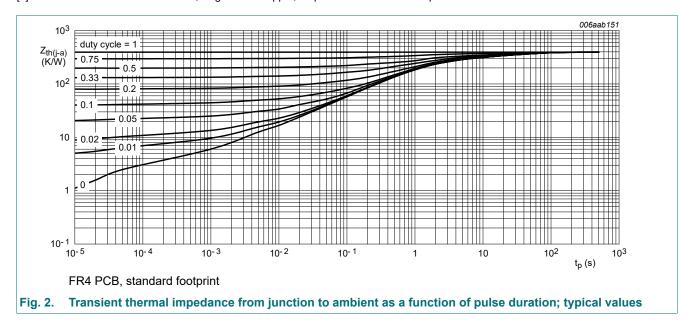
### 150 V, 1 A NPN high-voltage low VCEsat transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



## 150 V, 1 A NPN high-voltage low VCEsat transistor

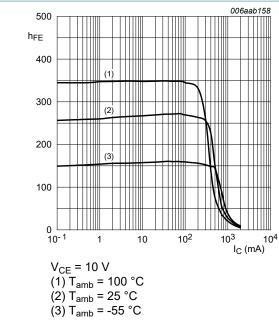
# 10. Characteristics

#### **Table 7. Characteristics**

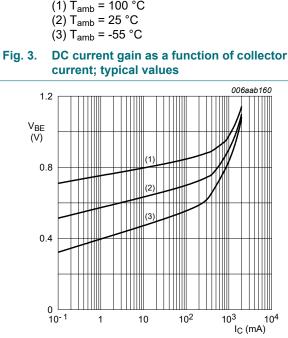
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
curr	current	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	250	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; T <sub>amb</sub> = 25 °C	100	250	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	50	160	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	40	60	mV
		I <sub>C</sub> = 100 mA; I <sub>B</sub> = 20 mA; T <sub>amb</sub> = 25 °C	-	33	50	mV
		$I_C = 1 \text{ A}$ ; $I_B = 200 \text{ mA}$ ; pulsed; $t_p \le$	-	225	350	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	1.1	1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	7	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	565	-	ns
t <sub>on</sub>	turn-on time		-	572	-	ns
t <sub>s</sub>	storage time		-	1530	-	ns
t <sub>f</sub>	fall time		-	700	-	ns
t <sub>off</sub>	turn-off time		-	2230	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	30	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	5.7	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	150	-	pF

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#### 150 V, 1 A NPN high-voltage low VCEsat transistor



current; typical values



 $V_{CE} = 10 V$ (1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. Base-emitter voltage as a function of collector current; typical values

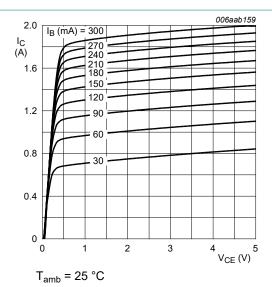
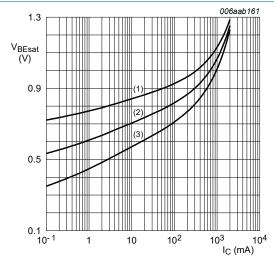


Fig. 4. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$ (1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

#### 150 V, 1 A NPN high-voltage low VCEsat transistor

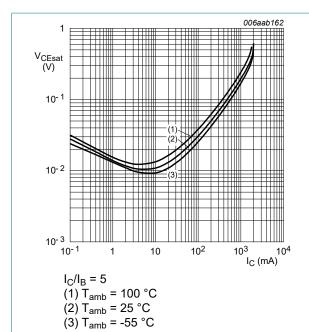


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

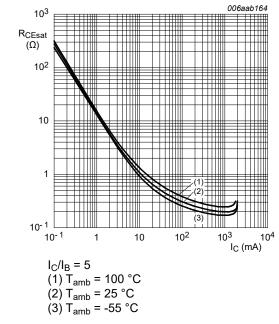


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

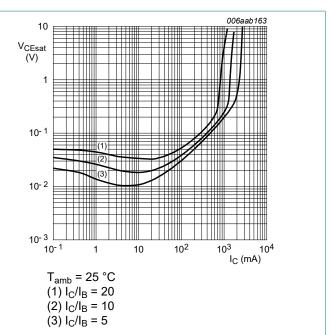


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

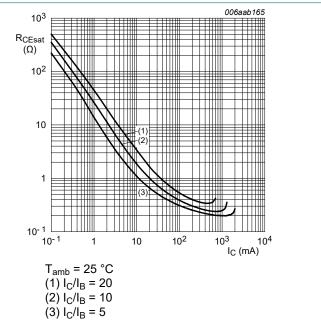
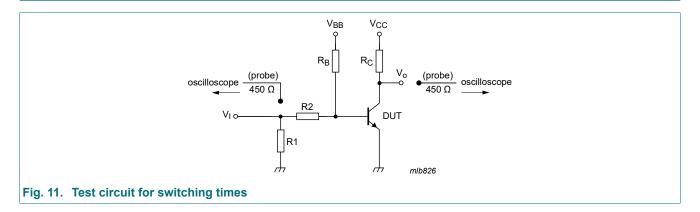


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

### 150 V, 1 A NPN high-voltage low VCEsat transistor

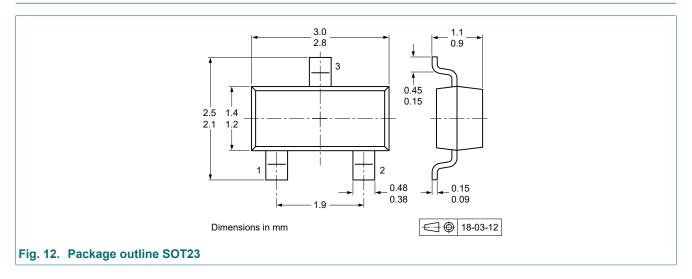
## 11. Test information



### **Quality information**

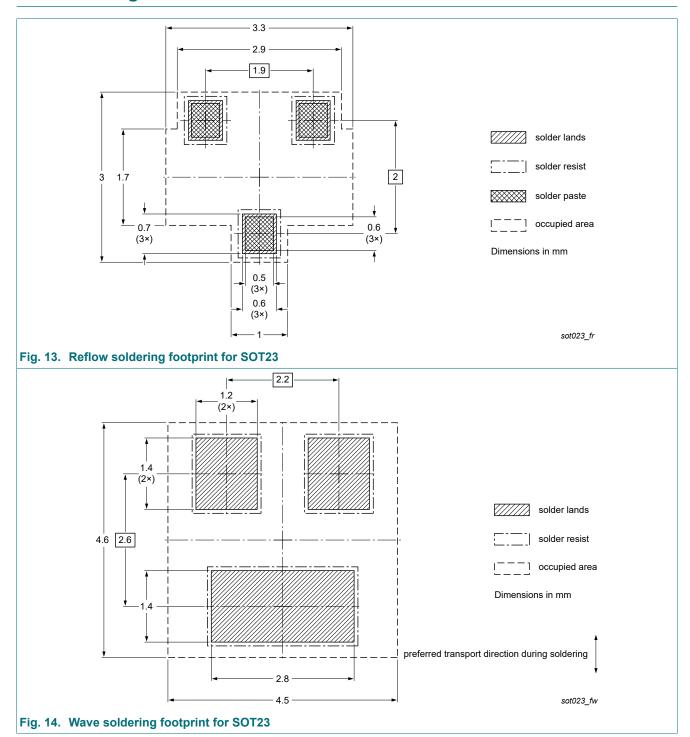
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



### 150 V, 1 A NPN high-voltage low VCEsat transistor

# 13. Soldering



150 V, 1 A NPN high-voltage low VCEsat transistor

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8115T-Q v.1	20220316	Product data sheet	-	-

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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